

## Abstract

In a method for producing an SOI wafer comprising steps of implanting hydrogen ions etc. from a surface of a bond wafer 21 to form an ion-implanted layer 24 inside the wafer, bonding the ion-implanted surface of the bond wafer and a surface of a base wafer 22 via an oxide film 23 or directly, and forming an SOI wafer by delaminating a part of the bond wafer at the ion-implanted layer by heat treatment, wherein a silicon wafer consisting of silicon single crystal grown by Chochralski method, which is occupied by N region outside OSF generated in a ring shape and has no defect region detected by Cu deposition method, is used as the bond wafer. Thereby, even in the case of forming an extremely thin SOI layer 27 such that, for example, its thickness is 200 nm or less, there is provided an SOI wafer which has an excellent electric property without causing micro pits by cleaning with hydrofluoric acid etc., and in addition, can be produced without increasing the number of process.